

# Citations for Ion : **Sn**

Pub. Year	Authors, Title, Journal Citation and Comments	Citation Numb
<b>1966</b>	VanLint, V. A. J. Wyatt, M. E. Schmitt, R. A. Suffredini, C. S. Nichols, D. K. 'Range of Photoparticle Recoil Atoms on Solids' <i>Phys. Rev.</i> , 147, 242-48 (1966) <i>Comment</i> : R. (.001- 5 epsilon) Ti, Sc, Cr, Fe, Mn, Ni, Co, Ge, Zr, Y, Sr, Mo, Rh, Pd, Ag, Cd, Sn, Gd, Ta, Au, Th -> Al, Cu	1966-VanL
<b>1976</b>	Harris, T. J. Sealy, B. J. Surridge, R. K. 'Effects of Channelling on the Electrical Properties of Donor Implanted GaAs' <i>Elec. Letters</i> , 12, 664-665 (1976) <i>Comment</i> : R. 90 keV Sn, 90-300 keV Te -> GaAs	1976-Harr
<b>1977</b>	Surridge, R. K. Sealy, B. J. 'A Comparison of Sn-, Ge-, Se-, and Te-Ion-Implanted GaAs' <i>Appl. Phys.</i> , 10, 911-917 (1977) <i>Comment</i> : R. 200 And 300 keV Sn, Ge, Se, Te -> GaAs	1977-Surr
<b>1977</b>	Surridge, R. K. Sealy, B. J. D'Cruz, A. D. E. Stephens, K. G. 'Annealing Kinetics of Donor Ions Implanted into GaAs' <i>Gallium Arsenide and Related Compounds (Edinburgh)</i> , Ed. by C. Hilsum, 161-167 (1977) <i>Comment</i> : R. 200 keV Se, Sn -> GaAs	1977-Surr2
<b>1977</b>	Surridge, R. K. Sealy, B. J. 'Active Layers for Device Applications by using High-Energy Selenium Implantation into GaAs' <i>Elec. Letters</i> , 13, 233-234 (1977) <i>Comment</i> : R. 150 keV Sn, 1 MeV Se -> GaAs	1977-Surr3
<b>1979</b>	Santry, D. C. Werner, R. D. Westcott, O. M. 'The Range of 120 keV Ions in Solids' <i>IEEE Trans. Nucl. Sci.</i> , Ns-26, 1331-1334 (1979) <i>Comment</i> : R, dR. 120 keV Mg, Al, P, S, Cl, K, Ar, Cr, Mn, Cu, Zn, Ga, As, Br, Kr, Rb, Ag, In, Sn, Sb, Te, I, Xe, Cs, Ba, Pr, Au, Hg, Tl, Pb, Bi -> Be, C, Al, Si	1979-Sant
<b>1985</b>	Behar, M. Fichtner, P. F. Olivieri, C. A. DeSouza, J. P. Zawislak, F. C. 'Range Profiles of 10-380 keV Sn and Cs into Amorphous Silicon' <i>Rad. Effects</i> , 90, 103-110 (1985) <i>Comment</i> : R, dR. Sn, Cs (10-380 keV) -> Si	1985-Beha2
<b>1986</b>	Geyer, E. Reschke, D. Freitag, K. 'Z1 Stopping Power Oscillation in the Nuclear Stopping Regime as Obtained by Time-of-Flight Spectroscopy of Heavy Ions in Hydrogen' <i>Nucl. Inst. Methods</i> , B15, 81-85 (1986) <i>Comment</i> : S. Heavy Ions (49-65) at 26 - 90 keV -> H2 (gas)	1986-Geye

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<b>Pub. Year</b>	<b>Authors, Title, Journal Citation and Comments</b>	<b>Citation Numb</b>
<b>1987</b>	Freitag, K. Reschke, D. Geyer, E. 'Stopping Power Measurements for Low Energy Ions in Gases by Time-of-Flight Spectroscopy' <i>Nucl. Inst. Methods, B27, 344-352 (1987)</i> <i>Comment : S. Heavy Ions (49-65) at 27 - 90 keV -&gt; H2 (gas)</i>	1987-Frei
<b>2000</b>	Vorobyova, I. V. Reimann, C. T. Toulemonde, M. 'Comparison of the Structure and Sizes of Tracks Induced by High Energy Monatomic and Cluster Ions Incident on the Surface of Mica' <i>Nucl. Inst. Methods, B166-167, 959-963 (2000)</i> <i>Comment : S. Sn (1 MeV/u), C(30 keV/u) -&gt; Mica</i>	2000-Voro

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